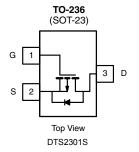


P-Channel 20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	- 20
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.120
$R_{DS(on)}(\Omega)$ at $V_{GS} = -2.5 \text{ V}$	0.180
I _D (A)	- 3.9
Configuration	Single

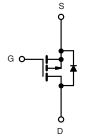


FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualified^d
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and Halogen-free	DTS2301S

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	- 20	V
Gate-Source Voltage		V_{GS}	± 8	V
Continuous Drain Current	T _C = 25 °C	- I _D	- 3.9	
	T _C = 125 °C		- 2.2	
Continuous Source Current (Diode Conduction) ^a		I _S	- 3.7	Α
Pulsed Drain Current ^b		I _{DM}	- 15	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 9	
Single Pulse Avalanche Energy	L=U.I MH	E _{AS}	4	mJ
Maximum Power Dissipation ^b	T _C = 25 °C		3	14/
	T _C = 125 °C	P_{D}	1	W
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	166	°C/W
Junction-to-Foot (Drain)		R_{thJF}	50	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static	•	•					
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA		- 20	-	=.	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = - 250 μA	- 0.45	-	- 1.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	= 0 V, V _{GS} = ± 8 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = - 20 V	-	-	- 1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 20 V, T _J = 125 °C	-	-	- 50	μΑ
		V _{GS} = 0 V	V _{DS} = - 20 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 4.5 V	$V_{DS} \ge 5 V$	- 8	-		Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V	I _D = - 2.8 A	-	0.080	0.120	Ω
		V _{GS} = - 2.5 V	I _D = - 2 A	-	0.110	0.180	
Forward Transconductance ^a	9fs	V _{DS} = - 1.6 V, I _D = - 2.8 A		-	7	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	340	425	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	= 0 V V _{DS} = - 10 V, f = 1 MHz	-	80	100	pF
Reverse Transfer Capacitance	C _{rss}			-	55	70	
Total Gate Charge ^c	Qg			-	5	8	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 4.5 V	$V_{DS} = -10 \text{ V}, I_{D} = -2.8 \text{ A}$	-	0.7	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	1.3	-	
Gate Resistance	R _g	f = 1 MHz		5.5	10	14.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	15	22	
Rise Time ^c	t _r	V_{DD} = - 10 V, R_L = 10 Ω $I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		-	14	21	- ns
Turn-Off Delay Time ^c	t _{d(off)}			-	30	45	
Fall Time ^c	t _f			-	9	15	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	- 15	Α
Forward Voltage	V _{SD}	l _F =	- 1.6 A, V _{GS} = 0	-	- 0.8	- 1.2	V

Notes

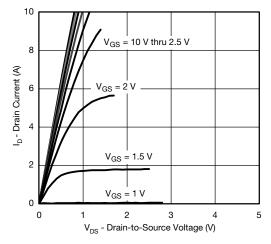
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

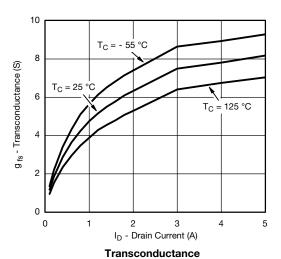
10

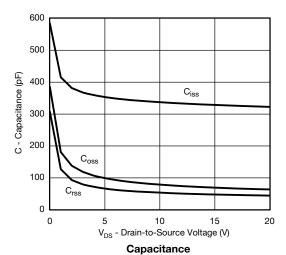


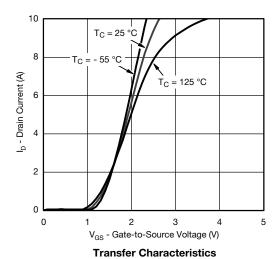
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

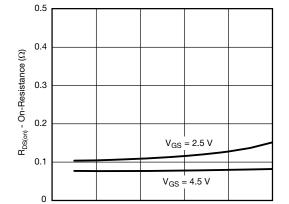


Output Characteristics





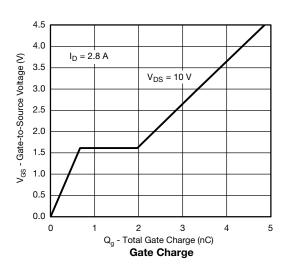




I_D - Drain Current (A)

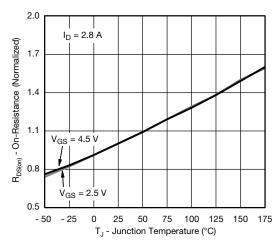
On-Resistance vs. Drain Current

0

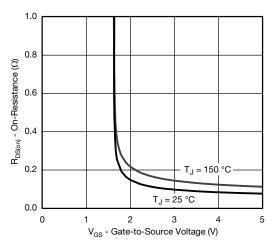




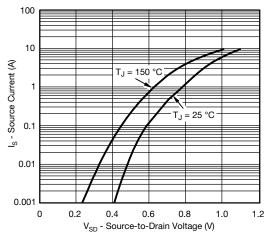
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



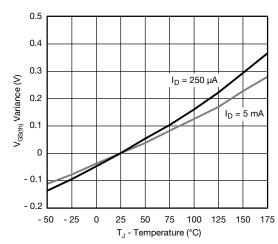
On-Resistance vs. Junction Temperature



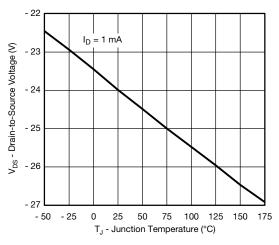
On-Resistance vs. Gate-to-Source Voltage



Source-Drain Diode Forward Voltage



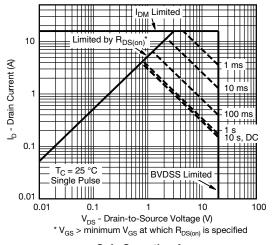
Threshold Voltage



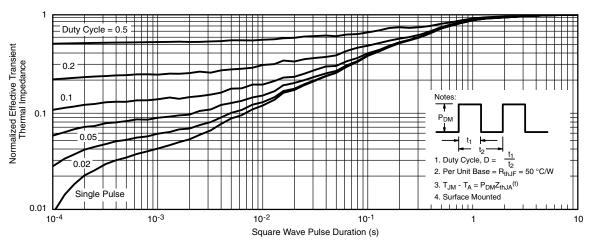
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



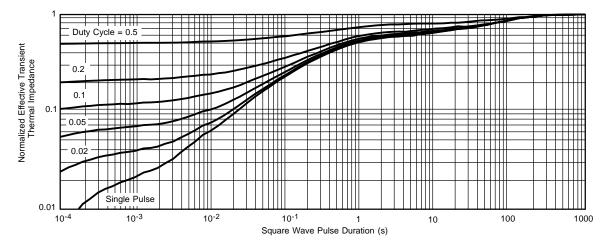
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Foot

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THERMAL RATINGS (T_A= 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

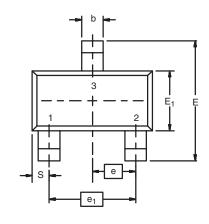
Note

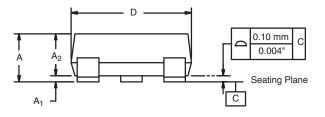
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

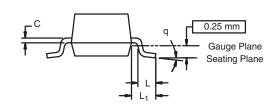
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



SOT-23 (TO-236): 3-LEAD





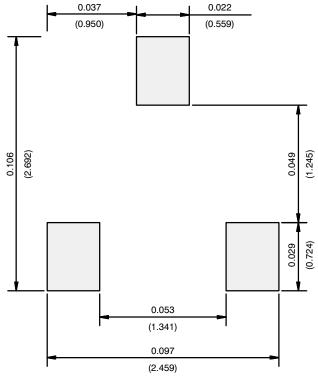


Dim -	MILLIM	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95	0.95 BSC		4 Ref	
e ₁	1.90 BSC		0.074	8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025	5 Ref	
S	0.50 Ref		0.020) Ref	
q	3°	8°	3°	8°	

DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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